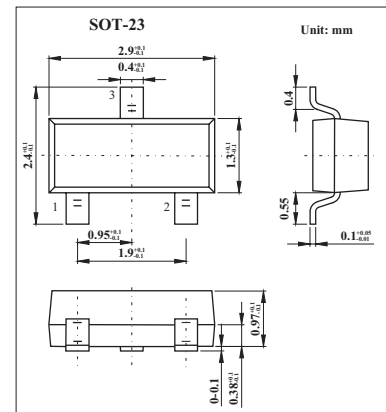


Silicon Schottky Barrier Diode

HSM88AS

■ Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_o	15	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1 \text{ mA}$	350		420	mV
		$I_F = 10 \text{ mA}$	500		580	
Reverse current	I_R	$V_R = 2 \text{ V}$			0.2	μA
		$V_R = 10 \text{ V}$			10	
Capacitance	C	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			0.85	pF
Capacitance deviation	ΔC	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			0.10	pF
Forward voltage deviation	ΔV_F	$I_F = 10 \text{ mA}$			10	mV
ESD-Capability (Note 1)		$C=200\text{pF}$, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geq 400\text{nA}$ at $V_R = 2 \text{ V}$

■ Marking

Marking	C1
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